

ELECTRONIC INFORMATION DISCLOSURE STATEMENT

Electronic Version v18

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Title of Invention

METHOD OF FORMING STRAINED SI/SIGE ON INSULATOR
WITH SILICON GERMANIUM BUFFER

Application Number : 10/710,255
Confirmation Number: 6/29/04
First Named Applicant: Huajie Chen
Attorney Docket Number: FIS920030381US1
Art Unit: 2813
Examiner:
Search string: (6603156 or 6524935).pn

US Patent Documents

Note: Applicant is not required to submit a paper copy of cited US Patent Documents

init	Cite.No.	Patent No.	Date	Patentee	Kind	Class	Subclass
CC	1	6603156	2003-08-05	Rim	B2	257	190
CC	2	6524935	2003-02-25	Canaperi, et al.	B1	438	458

Signature

Examiner Name	Date
Chandra Chaudhari	1-05